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SEMICONDUCTOR



ESD



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MOV



GDT



PLED

AONS21321-MS

Product specification

Description

The AONS21321 uses advanced trench technology excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a load switch or in PWM applications.

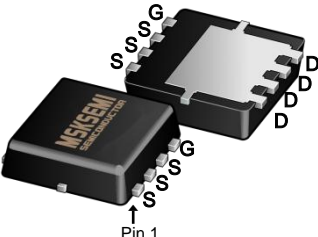
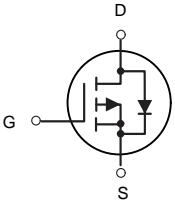

General Features

- $V_{DS} = -30V, I_D = -50A$
- $R_{DS(ON)} < 15m\Omega @ V_{GS} = -10V$
- $R_{DS(ON)} < 25m\Omega @ V_{GS} = -4.5V$
- High Power and current handling capability
- Lead free product is acquired
- Surface mount package

Application

- PWM applications
- Load switch
- Power management

Reference News

DFN5X6-8L	P-Channel MOSFET	Marking
		

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous ($T_C = 25^\circ C$)	-50	A
	Drain Current-Continuous ($T_C = 100^\circ C$)	-24	
I_{DM}	Drain Current-Pulsed (Note 1)	-80	A
P_D	Maximum Power Dissipation ($T_C = 25^\circ C$)	3	W
	Maximum Power Dissipation ($T_C = 100^\circ C$)	1.3	
EAS	Single pulse avalanche energy (Note 5)	231	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2)	41.67	$^\circ C/W$

Electrical Characteristics (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-30	-33	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1	-1.5	-3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-10A	-	9	15	mΩ
		V _{GS} =-4.5V, I _D =-7A	-	18	25	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-10V, I _D =-10A	-	20	-	S
Input Capacitance	C _{iss}	V _{DS} =-15V, V _{GS} =0 V, F=1.0MHz	-	1750	-	PF
Output Capacitance	C _{oss}		-	215	-	PF
Reverse Transfer Capacitance	C _{rss}		-	180	-	PF
Turn-on Delay Time	t _{d(on)}	V _{DD} =-15V, I _D =-10A, V _{GS} =-10V, R _{GEN} =1 Ω	-	9	-	nS
Turn-on Rise Time	t _r		-	8	-	nS
Turn-Off Delay Time	t _{d(off)}		-	28	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Q _g	V _{DS} =-15V, I _D =-10A, V _{GS} =- 10V	-	24	-	nC
Gate-Source Charge	Q _{gs}		-	3.5	-	nC
Gate-Drain Charge	Q _{gd}		-	6	-	nC
Diode Forward Current (Note 2)	I _S		-	-	-12	A
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-12A	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. E_{AS} condition: T_j=25℃, V_{DD}=-15V, V_G=10V, L=0.5mH, R_g=25Ω, I_{AS}=-34A

Typical Electrical and Thermal Characteristics

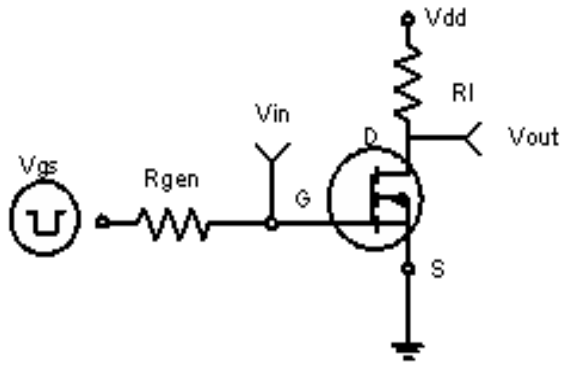


Figure 1: Switching Test Circuit

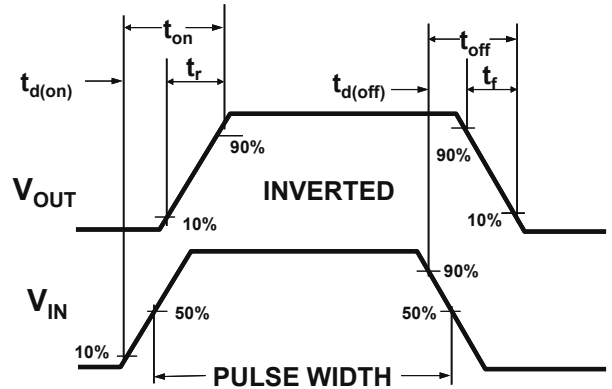


Figure 2: Switching Waveforms

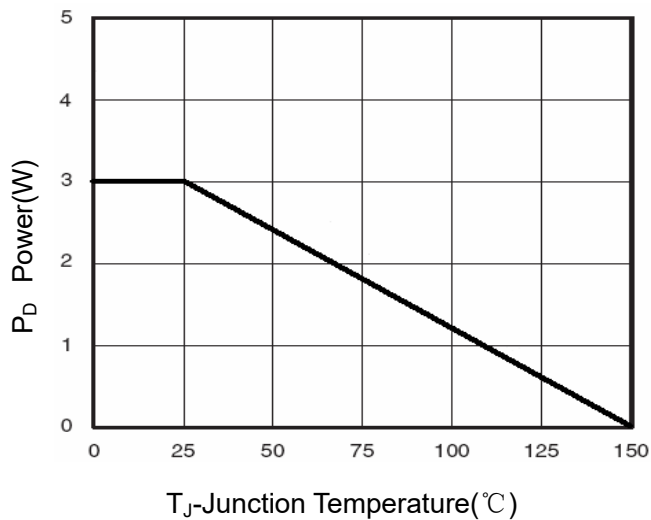


Figure 3 Power Dissipation

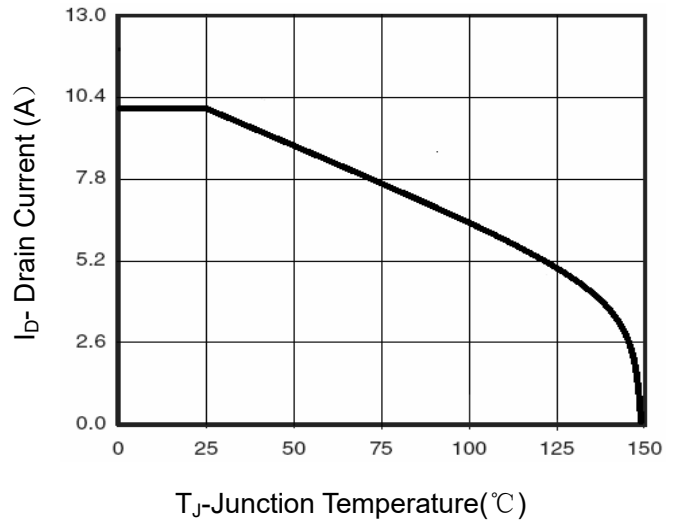


Figure 4 Drain Current

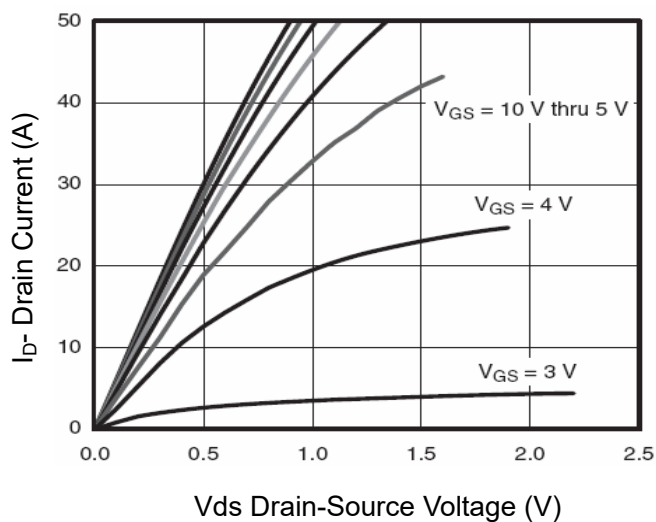


Figure 5 Output Characteristics

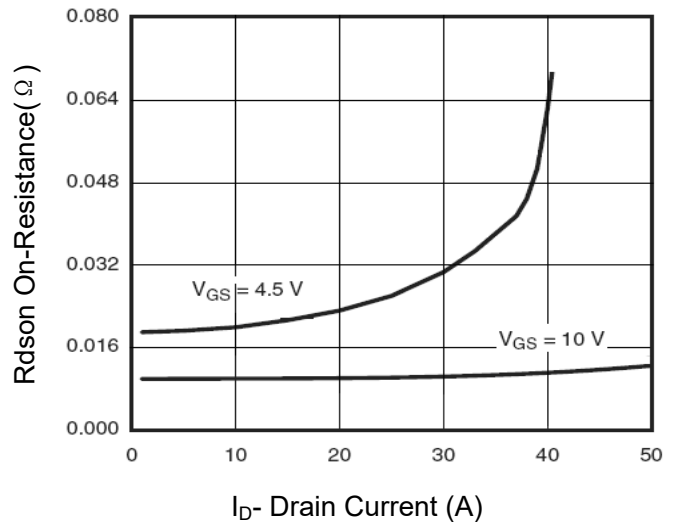


Figure 6 Drain-Source On-Resistance

Figure 5 Output Characteristics

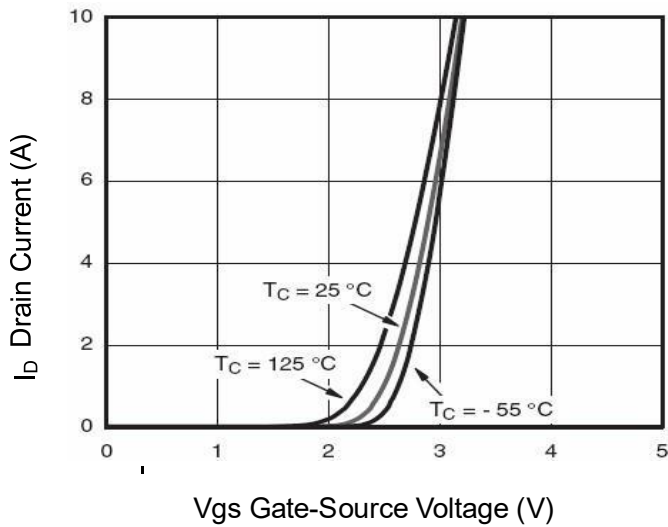


Figure 7 Transfer Characteristics

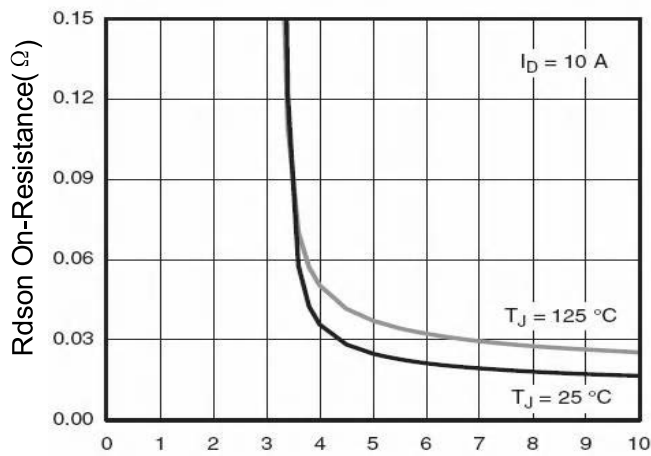


Figure 9 Rdson vs Vgs

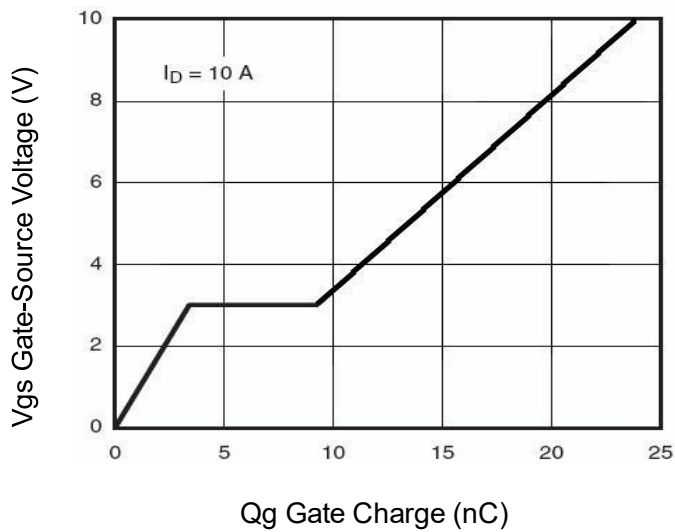


Figure 11 Gate Charge

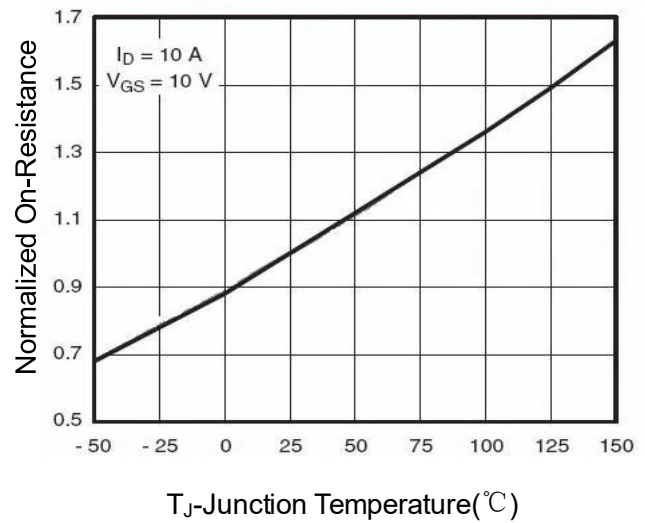


Figure 8 Drain-Source On-Resistance

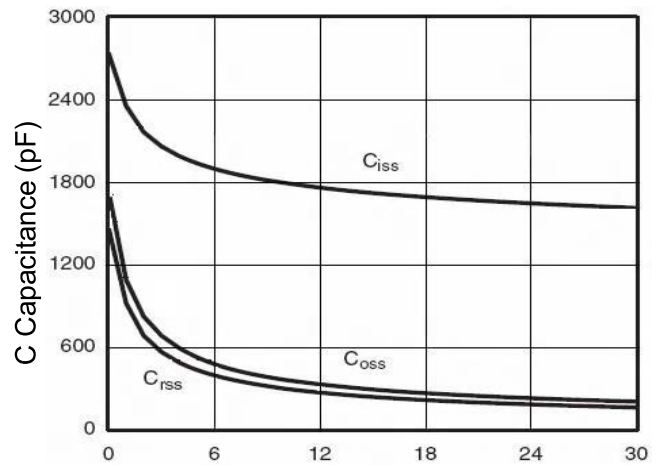


Figure 10 Capacitance vs Vds

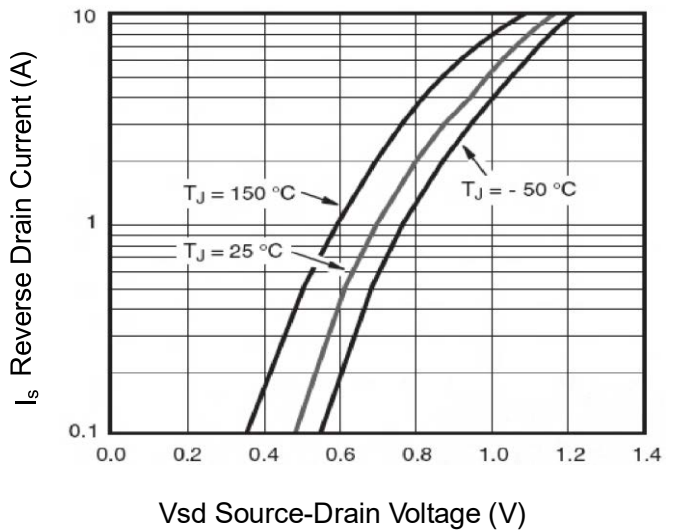


Figure 12 Source- Drain Diode Forward

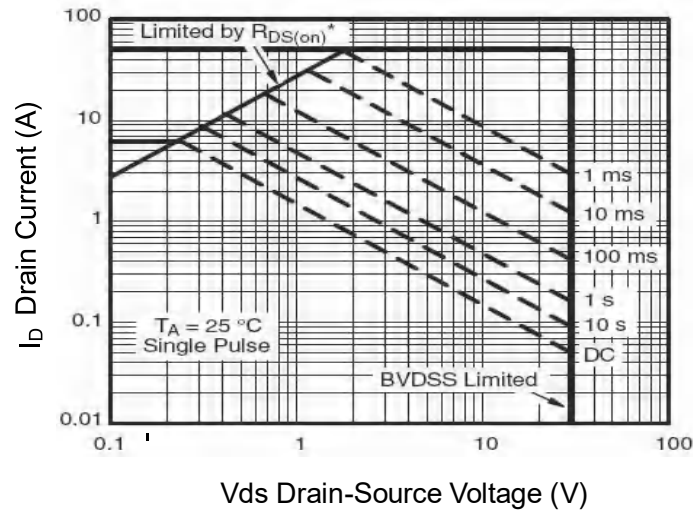


Figure 13 Safe Operation Area

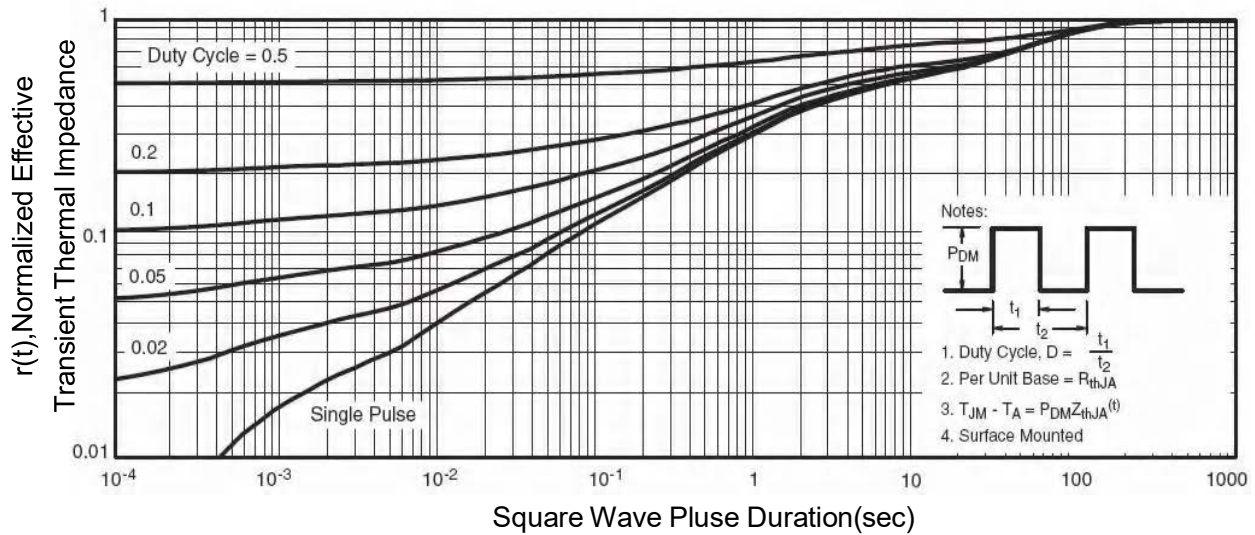
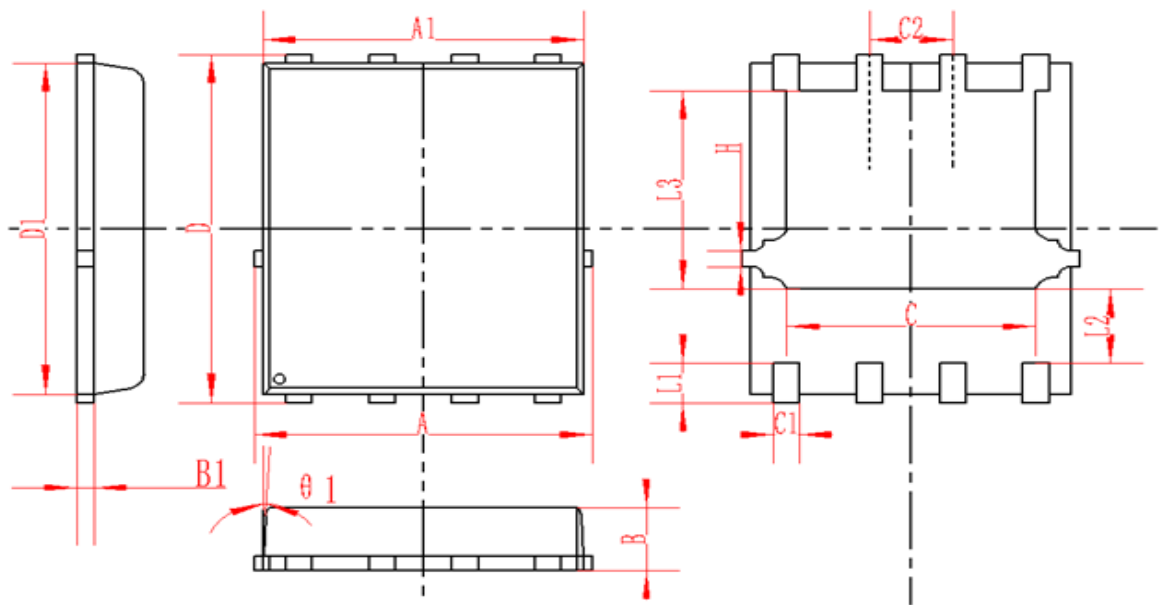


Figure 14 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Information



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
B	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF			0.010REF		
C	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2	1.27TYP			0.5TYP		
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
H	0.24	0.25	0.26	0.009	0.010	0.010

REEL SPECIFICATION

P/N	PKG	QTY
AONS21321-MS	DFN5X6-8L	5000

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